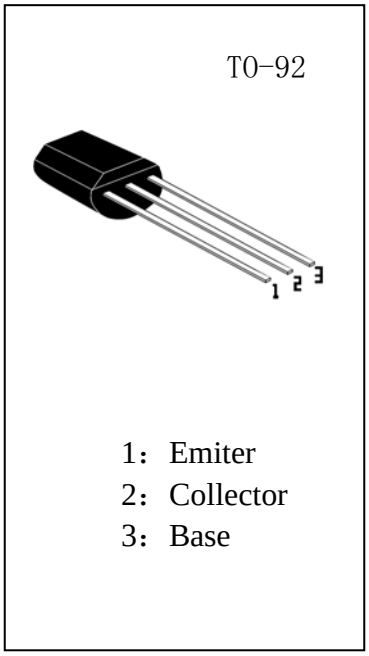
CHANG JIANG
ELECTRONICS CO., LTD.

2SA1015

LOW FREQUENCY TRANSISTOR

- Ic=-150mA, Ib=-50mA
- Vcbo=-50V
- 与 2SC1815 对管



极限参数(Absolute Maximum Ratings) Ta=25^{0}C

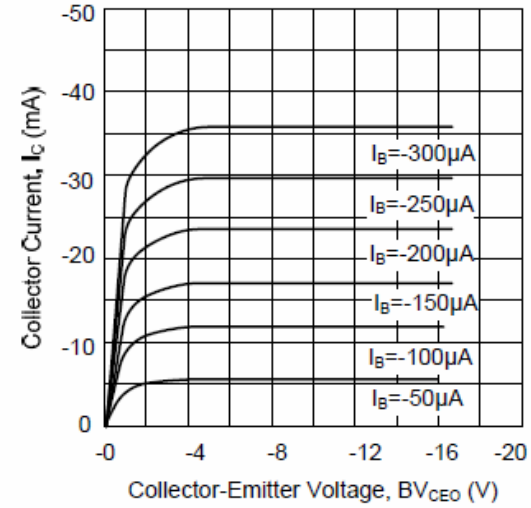
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	**-50**	V
Collector-Emitter Voltage	Vceo	**-50**	V
Emitter-Base Voltage	Vebo	**-5**	V
Collector Current	Ic	**-150**	mA
Base current	Ib	**-50**	mA
Collector Dissipation	Pc	**400**	m W
Junction Temperature	Tj	**150**	^{0}C
Storage Temperature	Tstg	**-55~150**	^{0}C

电性能(Electrical Characteristic) Ta=25^{0}C

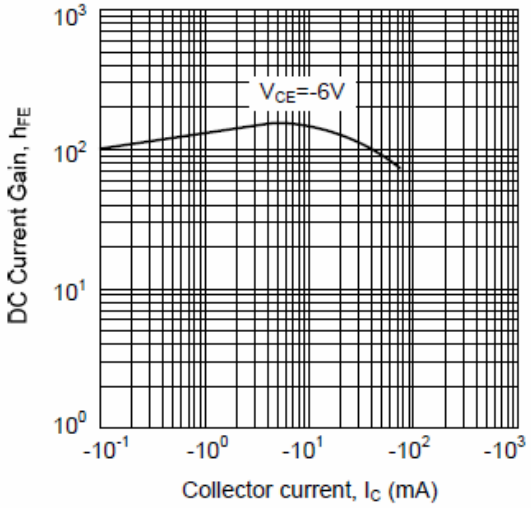
Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BVcbo	Collector-Base Breakdown Voltage	Ic=-100uA Ie=0	-50			V
BVceo	Collector-Emitter Breakdown Voltage	Ic=-1mA Ib=0	-50			V
BVebo	Emitter-Base Breakdown Voltage	Ie=-100uA Ic=0	-5			V
Icbo	Collector Cutoff Current	Vcb=-50V, Ie=0			-100	nA
Iebo	Emitter Cutoff Current	Veb=-5V, Ic=0			-100	nA
Iceo	Collector Cutoff Current	Vce=-50V, Ib=0			-10	uA
Vce(sat)	Collector-Emitter Saturation Voltage	Ic=-100mA, Ib=-10mA			-0.3	V
Vbe(sat)	Base-Emitter Saturation Voltage	Ic=-100mA, Ib=-10mA			-1.1	V
Hfe1	DC Current Gain	Vce=-6V, Ic=-150mA	25			
Hfe2	DC Current Gain	Vce=-6V, Ic=-2mA	70		800	
Cob	Output Capacitance	Vcb=-10V, Ie=0,f=1MHz			7	PF
fT	Current Gain-Bandwidth product	Vce=-10V, Ic=-1mA,	80			MHz
NF	Noise Figure	Ic=-100uA, Vce=6V f=1kHz, Rg=10kΩ		0.5	6	dB

CLASS	O	Y	GR			BL		
Hfe2	70-140	120-240	200-240	240-350	350-400	350-450	450-600	600-700

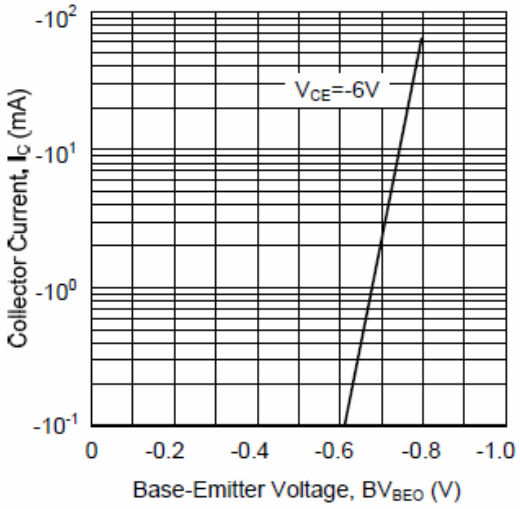
Static characteristics



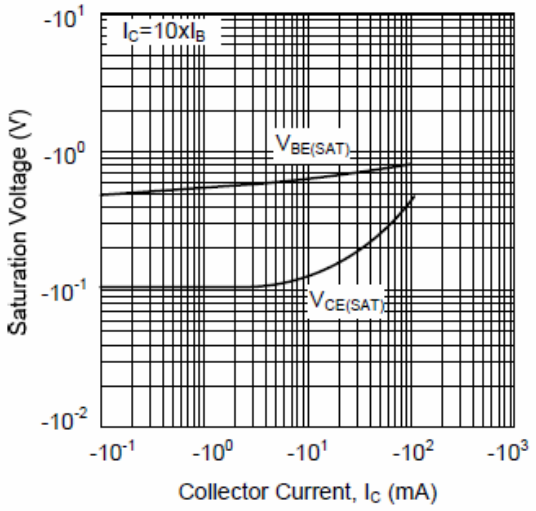
DC Current Gain



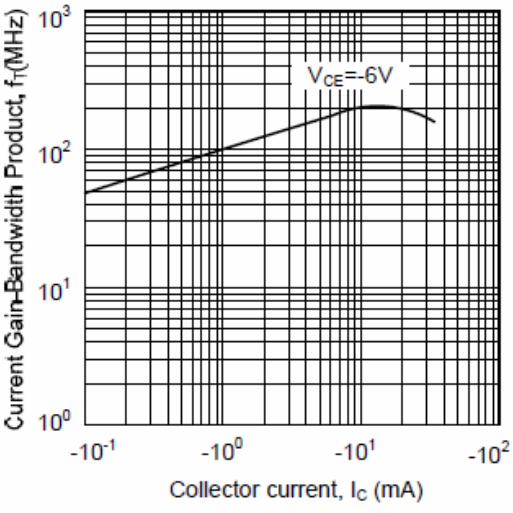
Base-Emitter on Voltage



Saturation voltage



Current Gain-Bandwidth Product



Collector Output Capacitance